

Silicon NPN Power Transistors

2SC1185

DESCRIPTION

- With TO-3 package
- Wide area of safe operation
- High breakdown voltage
:V_{CEO}=250V(min)

APPLICATIONS

- For voltage regulator,inverter,switching mode power supply applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

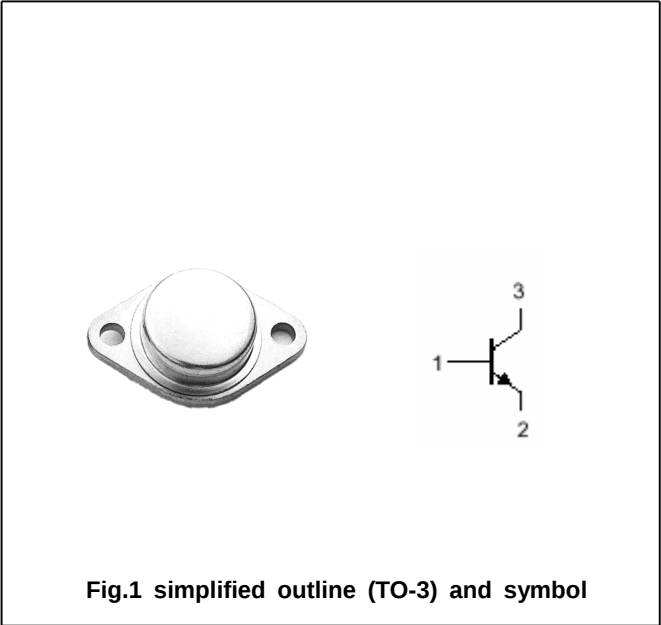


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	250	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		0.7	A
P _D	Total power dissipation	T _C =25?	50	W
T _J	Junction temperature		150	?
T _{stg}	Storage temperature		-55~150	?

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CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=30mA; I_B=0$	250			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA; I_E=0$	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=500mA; I_B=100mA$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=500mA; I_B=100mA$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			10	μA
h_{FE}	DC current gain	$I_C=0.4A; V_{CE}=10V$	40		200	

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PACKAGE OUTLINE

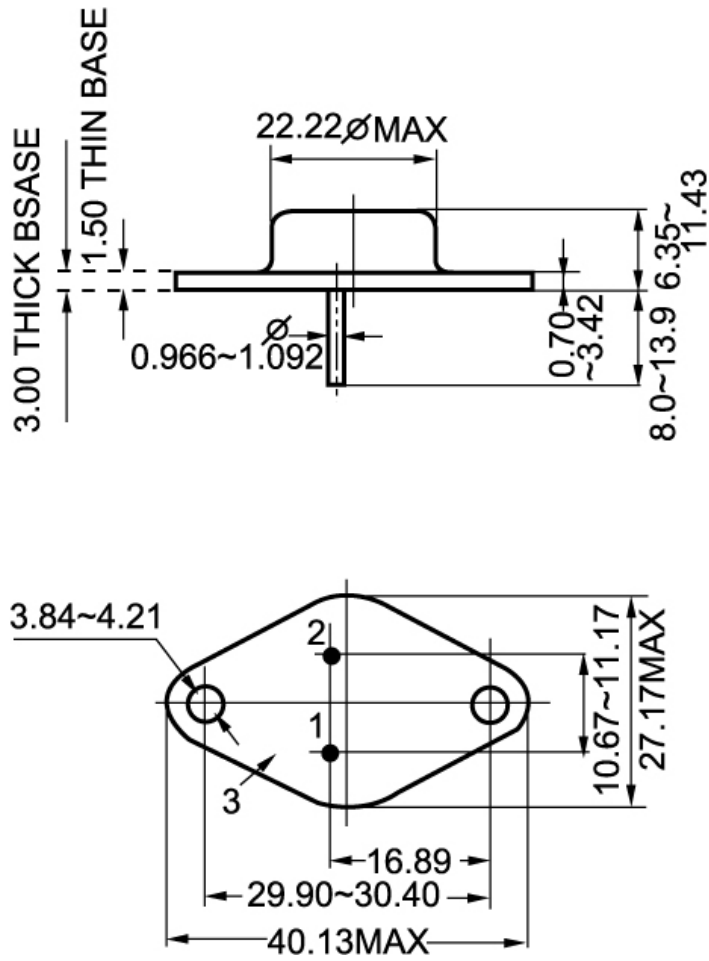


Fig.2 outline dimensions